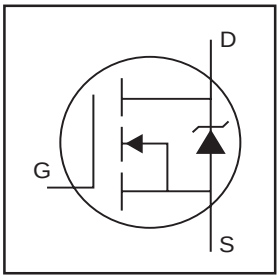
International
IOR Rectifier

PD - 95583

IRLZ34NSPbF
IRLZ34NLPbF

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- Surface Mount (IRLZ34NS)
- Low-profile through-hole (IRLZ34NL)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



V_{DSS} = 55V

$R_{DS(on)}$ = 0.035Ω

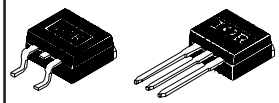
I_D = 30A

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D^2Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D^2Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRLZ34NL) is available for low-profile applications.



D^2Pak TO-262

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V⑤	30	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V⑤	21	
I_{DM}	Pulsed Drain Current ①⑤	110	
P_D @T_A = 25°C	Power Dissipation	3.8	W
P_D @T_C = 25°C	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	±16	V
E_{AS}	Single Pulse Avalanche Energy②⑤	110	mJ
I_{AR}	Avalanche Current①	16	A
E_{AR}	Repetitive Avalanche Energy①	6.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

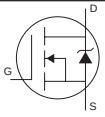
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–––	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted,steady-state)**	–––	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.065	–––	V/°C	Reference to 25°C, I_D = 1mA⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.035	Ω	V_{GS} = 10V, I_D = 16A ④
		–––	–––	0.046		V_{GS} = 5.0V, I_D = 16A ④
		–––	–––	0.060		V_{GS} = 4.0V, I_D = 14A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	–––	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	11	–––	–––	S	V_{DS} = 25V, I_D = 16A⑤
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	µA	V_{DS} = 55V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 16V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -16V
Q_g	Total Gate Charge	–––	–––	25	nC	I_D = 16A
Q_{gs}	Gate-to-Source Charge	–––	–––	5.2		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	14		V_{GS} = 5.0V, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	–––	8.9	–––	ns	V_{DD} = 28V
t_r	Rise Time	–––	100	–––		I_D = 16A
$t_{d(off)}$	Turn-Off Delay Time	–––	21	–––		R_G = 6.5Ω, V_{GS} = 5.0V
t_f	Fall Time		29			R_D = 1.8Ω, See Fig. 10 ④⑤
L_S	Internal Source Inductance	–––	7.5	–––	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	–––	880	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	220	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	94	–––		f = 1.0MHz, See Fig. 5⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	30	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	110		
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 16A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	76	110	ns	T_J = 25°C, I_F = 16A
Q_{rr}	Reverse Recovery Charge	–––	190	290	nC	di/dt = 100A/µs ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = 25V, starting T_J = 25°C, L =610µH R_G = 25Ω, I_{AS} = 16A. (See Figure 12)

③ I_{SD} ≤ 16A, di/dt ≤ 270A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C

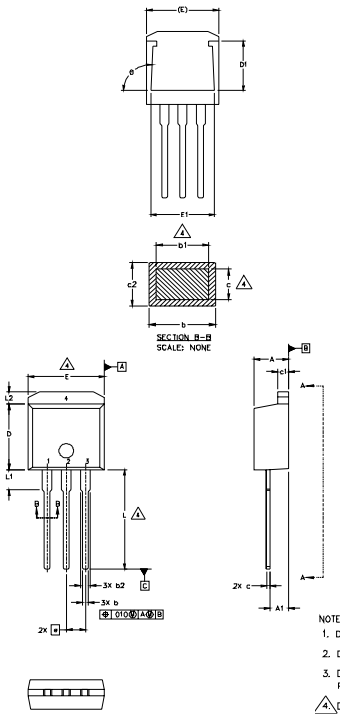
④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ Uses IRLZ34N data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

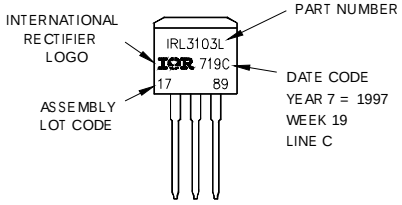
HEXFET	IGBT
1.– GATE	1 - GATE
2.– DRAIN	2 - COLLECTOR
3.– SOURCE	3 - EMITTER
4.– DRAIN	

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



OR